# MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

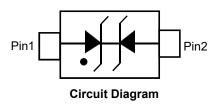
**PLED** 

# Broduct data sheet





**SOD-323** 



#### **Feature**

- 2000W Peak pulse power per line (t<sub>P</sub> = 8/20µs)
- SOD-323 package
- Response time is typically < 1 ns
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD)
  ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

#### **Applications**

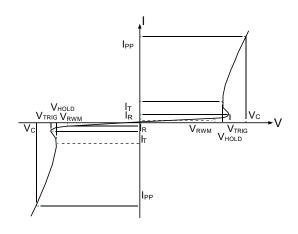
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

#### **Mechanical Characteristics**

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260 ℃
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- Pin flatness:≤3mil

#### **Electronics Parameter**

Symbol	Parameter
$V_{RWM}$	Peak Reverse Working Voltage
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
<b>I</b> PP	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
P <sub>PP</sub>	Peak Pulse Power
Сл	Junction Capacitance



# Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power ( t <sub>P</sub> = 8/20μS )	P <sub>pp</sub>	2000	W
Total Device Dissipation FR-5 Board	P <sub>D</sub>	500	mW
Lead Soldering Temperature	T∟	260 (10 sec)	°C
Operating Temperature	TJ	-55 to 150	°C
Storage Temperature	T <sub>STG</sub>	-55 to 150	°C

# Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Working Voltage <sup>(1)</sup>	V <sub>RWM</sub>				4.5	V
Breakdown Voltage(Pin1 to Pin2)	V <sub>BR</sub>	I <sub>t</sub> =1mA	4.6	5.3	6.1	V
Reverse Leakage Current (Pin1 to Pin2)	I <sub>R</sub>	V <sub>RWM</sub> =4.5V			2	μA
Clamping Voltage(Pin1 to Pin2)	Vc	I <sub>PP</sub> =20A t <sub>P</sub> = 8/20μs		7.5	8.5	V
Clamping Voltage(Pin1 to Pin2)	Vc	I <sub>PP</sub> =45A t <sub>P</sub> = 8/20μs		8.8	10	V
Clamping Voltage(Pin1 to Pin2)	Vc	I <sub>PP</sub> =90A t <sub>P</sub> = 8/20μs		11	12.5	V
Clamping Voltage(Pin1 to Pin2)	Vc	I <sub>PP</sub> =130A t <sub>P</sub> = 8/20μs		14	16	V
Junction Capacitance	C <sub>j</sub>	V <sub>R</sub> =0V f = 1MHz		320	360	pF

Note 1: V<sub>RWM</sub> is the maximum reverse working voltage, or reverse stand-off voltage. ESD can protect signal line properly within its rated voltage. If the signal line's voltage is over  $V_{\text{RWM}}$ , ESD will change to other state.

# **Typical Characteristics**

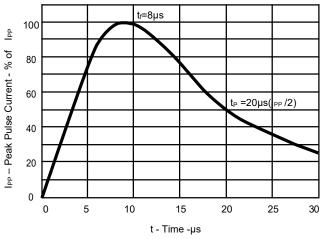


Fig 1.Pulse Waveform

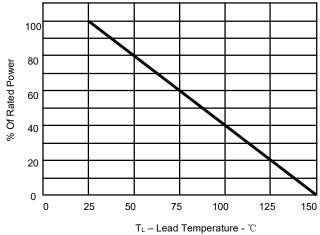


Fig 2.Power Derating Curve

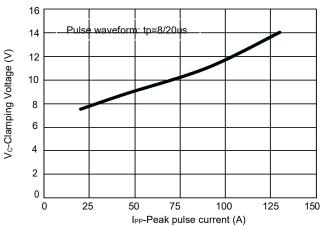


Fig 3. Clamping voltage vs. Peak pulse current

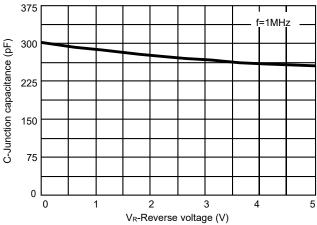


Fig 4. Capacitance vs. Reveres voltage

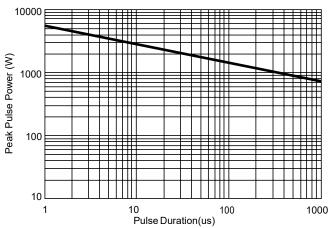
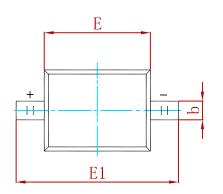
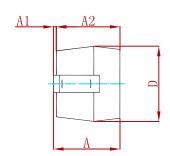


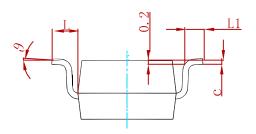
Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time



# PACKAGE MECHANICAL DATA

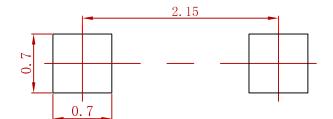






Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α		1.000		0.039	
A 1	0.000	0.100	0.000	0.004	
A2	0.800	0.900	0.031	0.035	
b	0.250	0.350	0.010	0.014	
С	0.080	0.150	0.003	0.006	
D	1.200	1.400	0.047	0.055	
E	1.600	1.800	0.063	0.071	
E1	2.550	2.750	0.100	0.108	
L,	0.475 REF.		0.019	REF.	
L1	0.250	0.400	0.010	0.016	
θ	0°	8°	0°	8°	

# **Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
PTVSHC3D4V5B-MS	SOD-323	3000



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